

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5320	MRAM or (magnetoresistive adj5 random adj5 access adj5 memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:19
L2	338	1 same (control adj3 circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:20
L3	74	2 same (npn or transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:20
L4	50	3 same (voltage or power or potential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:21
L5	46	4 and "365"/\$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:37
L6	4	1 same (control adj2 circuit) same (n\$1channel adj3 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:40
L7	29	1 and (control adj2 circuit) same (n\$1channel adj3 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:43
L9	161	1 and (control adj2 circuit) and (n\$1channel adj3 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:44

L11	0	9 and (control adj2 circuit).drwd. and (n\$1channel adj3 transistor). drwd.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:45
L12	31	9 and (control adj2 circuit).drwd.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 12:54
L13	9833	(control or controller or controlling) near5 ((n adj4 transistor) or NPN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 13:10
L14	1	13 near 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 13:10
L15	5	13 near20 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 13:17
L16	8	theel-wayne.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 13:17
L17	5	theel-wayne-\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/29 13:17